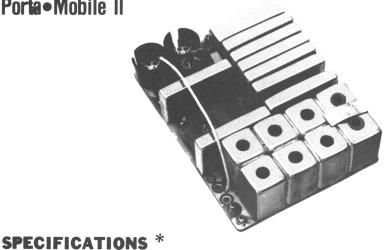


406-470 MHz RECEIVER

ER-60-A & ER-131-B FOR PE MODELS AND Porta•Mobile II



Type Numbers

Audio Output (EIA)

Channel Spacing

Sensitivity
12 dB SINAD (EIA
Method)
20 dB Quieting Method

Selectivity EIA Two-Signal

20 dB Quieting Method

Spurious Response

Intermodulation (EIA)

Audio Response

Modulation Acceptance

Squelch Sensitivity Critical Squelch Maximum Squelch

Maximum Frequency Spacing Frequency Range

> 406-420 MHz & 420-450 MHz 450-460 MHz 460-470 MHz

ER-60-A & ER-131-B

500 milliwatts at less than 5% distortion

25 kHz

 $\begin{array}{ccc} 0.35 & \mu V \\ 0.5 & \mu V \end{array}$

-65 dB at ± 25 kHz

-90 dB at ± 25 kHz

-60 dB

-65 dB

+2 and -10 dB of a standard 6 dB per octave deemphasis curve form 300 to 3000 Hz (1000 Hz reference)

±7.0 kHz

0.20 μV Greater than 20 dB Quieting

No Degradation (Sensitivity)

1.62 MHz 1.80 MHz 1.84 MHz 1 dB Degradation (Sensitivity)

3.25 MHz 3.60 MHz 3.68 MHz

*These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

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WARNING

No one should be permitted to handle any portion of the equipment that is supplied with high voltage; or to connect any external apparatus to the units while the units are supplied with power. KEEP AWAY FROM LIVE CIRCUITS.

DESCRIPTION

Receiver Models 4ER60A10-13, and receiver type ER131B are single conversion, superheterodyne FM receivers for operation on the 406-420, 420-450 MHz and 450-470 MHz bands. The complete receiver mounts on a single printed wiring board, and utilizes both discrete components and Integrated Circuit modules. The application of each model receiver is shown in the following Chart:

Model	Freq.	Number	Tone		
No.	Range	of Freqs.	Option		
4ER60A10 4ER60A11 4ER60A12 4ER60A13 ER131B	406-420 MHz 450-470 MHz 406-420 MHz 450-470 MHz 420-450 MHz	1 or 2	Chan. Gd. Chan. Gd. Chan. Gd.		

References to symbol numbers mentioned in the following text are found on the Schematic Diagram, Outline Diagram and Parts List (see Table of Contents). The typical circuit diagrams used in the test are representative of the circuits used in the Integrated Circuit modules. A block diagram of the receiver is shown in Figure 1.

Supply voltage for the receiver includes a continuous regulated 5.4 Volts for the compensator module, a continuous 7.5 Volts for the squelch module, and a switched 7.5 Volts for the remaining receiver stages.

CIRCUIT ANALYSIS

OSCILLATOR MODULE

The oscillator module consists of a crystal-controlled Colpitts oscillator similar to the oscillator module used in the transmitter (see Figure 2). The entire oscillator is contained in a metal can with with receiver operating frequency printed on the top. The crystal frequency ranges from 19.33 to 22.38 MHz, and the crystal frequency is multiplied 21 times.

The oscillator frequency is temperature compensated to provide instant frequency compensation, with a frequency stability of $\pm .0002\%$ from 0°C to +55°C and $\pm .0005\%$ from -30°C to +60°C. The temperature compensation network is contained in Compensator Module A313.

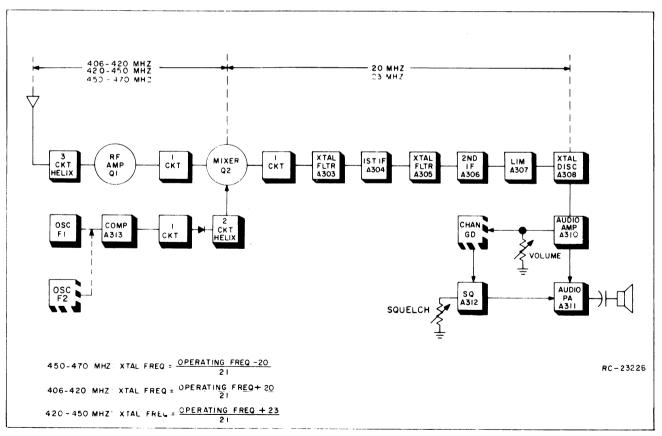


Figure 1 - Receiver Block Diagram

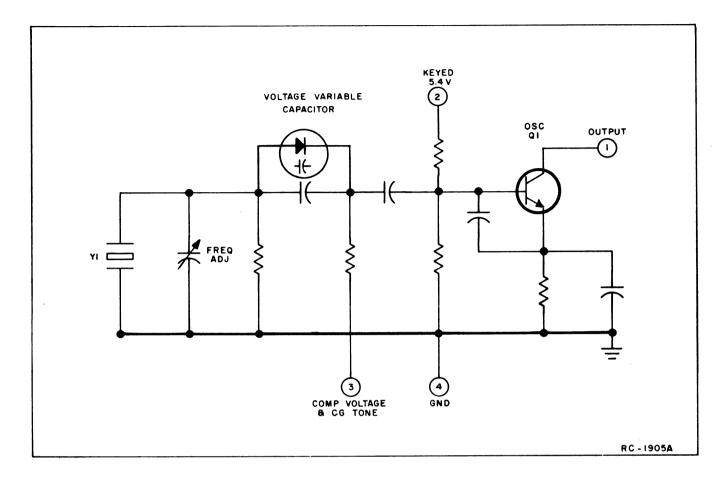


Figure 2 - Typical Oscillator Circuit

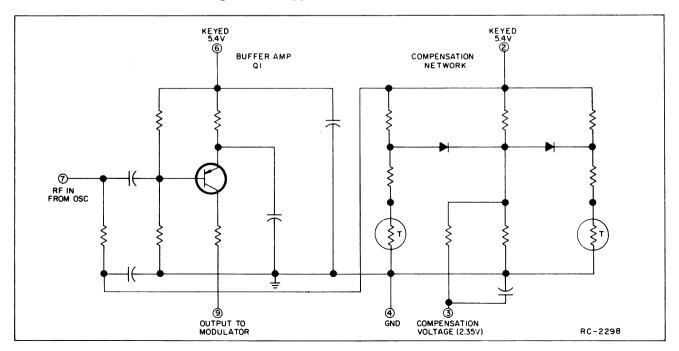


Figure 3 - Typical Compensator Circuit

In single frequency receivers, a jumper from H10 to H11 on System Board A702 connects the oscillator module to the continuous 5.4 volt supply voltage. The oscillator output is applied to Compensator A313.

In two-frequency receivers, an additional oscillator module is mounted on the receiver board. The single-frequency supply jumper is removed, and the proper frequency is selected by connecting the 5.4 Volts to the selected oscillator module through frequency selector switch S1 on the control unit.

— NOTE -

All oscillator modules are individually compensated at the factory and cannot be repaired in the field. Any attempt to remove the oscillator cover will void the warranty.

COMPENSATOR A313

Compensator module A313 contains a buffer-amplifier stage and the temperature compensation network for the oscillator. (see Figure 3)

RF from the oscillator is coupled through a DC blocking capacitor to the base of Ql. The output of Ql connects to multiplier coil Ll on the Multiplier assembly.

In the compensation network, the regulated 5.4 Volts at Pin 2 is applied to a thermistor-compensated voltage divider. The output at Pin 3 (2.35 Volts measured with a VTVM) is applied to Pin 3 and to the varactor in the Oscillator module. At temperatures below -10°C, the compensated voltage increases to maintain the proper voltage on the oscillator voltage-variable capacitor.

SERVICE NOTE —

An abnormally low VTVM reading (or no reading) at Pin 3 may indicate a short or leakage path in the oscillator. This can be checked by unsoldering Pin 3, raising it off of the printed board and taking another reading. If this reading is normal, the problem is in the Oscillator module. If the reading remains low (or zero), the problem is in the Compensator.

FRONT END A316/A317/A333

The receiver Front End consists of three tuned helical resonators and an RF amplifier stage. The RF signal from the antenna is coupled through RF cable W301 to a tap on L11/L16/L28. The tap is positioned to provide the proper impedance match to the antenna. RF energy is coupled to the third coil (L13/L18/L30) through openings in the sides of the cans. RF is then coupled from a tap on L13/L18/L30 through C8 to the base of RF amplifier Q1. The output of Q1 is developed across tuned circuit C9/C10 and L3, and is applied to the base of the mixer.

MULTIPLIER & MIXER

The output of the Compensator module is applied to L1 in the Multiplier assembly. L1 is tuned to three times the crystal frequency and is metered at the Mult Test Point (H8) on the receiver board. The output of L1 is applied to the anode of multiplier diode CR1. The two-helical resonators following CR1 are tuned to seven times the first multiplier frequency for a total multiplication of 21 times. The output of the helical resonators is direct-coupled to the emitter of the mixer transistor. In 406-420 MHz and 420-450 MHz receivers, a high side injection frequency is used. In 450-470 MHz receivers, a low side injection frequency is used.

The RF signal from the RF amplifier is applied to the base of mixer Q1 and the high or low side injection voltage from the multiplier assembly is applied to the emitter. The resultant 20 MHz IF frequency is coupled through the mixer collector tank (L2 & C6) to Crystal Filter A303. The collector tank also provides impedance matching to the crystal filter.

CRYSTAL FILTERS A303 & A305

Filter A303 follows the Multiplier-Mixer stage, and its output is applied to the 1st IF amplifier module. Filter A305 follows the IF Amplifier module. The two Crystal Filter provide the major selectivity for the receiver. A303 provides a minimum of 40 dB stop-band attenuation, while A305 provides a minimum of 20 dB stop-band attenuation.

IF AMPS A304 & A306

An IF Amplifier module follows each of the crystal filters, and contains the resistor-matching networks for the filters. A typical IF amplifier circuit is shown in Figure 4.

Each of the IF Amplifier modules consists of three R-C coupled amplifier stages that the DC series-connected for reduced drain. The two IF modules provide a total gain of approximately 85 dB.

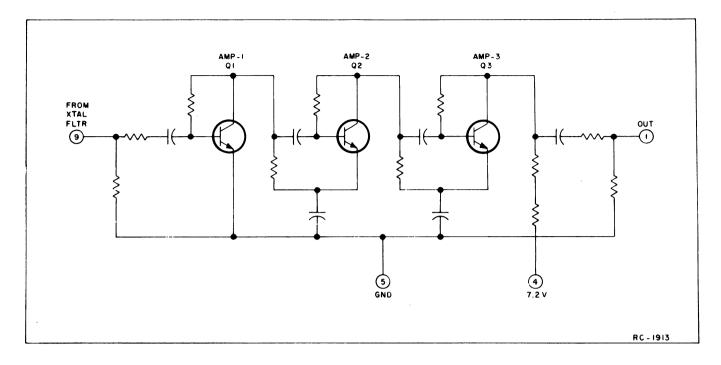


Figure 4 - Typical IF Amplifier Circuit

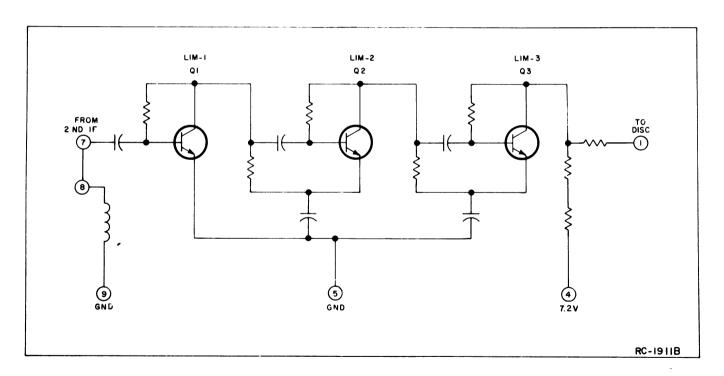


Figure 5 - Typical Limiter Circuit

LIMITER A307 & DISCRIMINATOR A308

Limiter A307 consists of three R-C coupled limiter stages that are DC series connected for reduced drain. The Limiter module also provides some gain. The output of the Limiter is applied to the

discriminator. A typical Limiter circuit is shown in Figure 5.

The receiver uses a 20 MHz, fixed-tuned crystal discriminator (A308) to recover the audio from the IF signal. The Discriminator output is applied to the Audio Amplifier module.

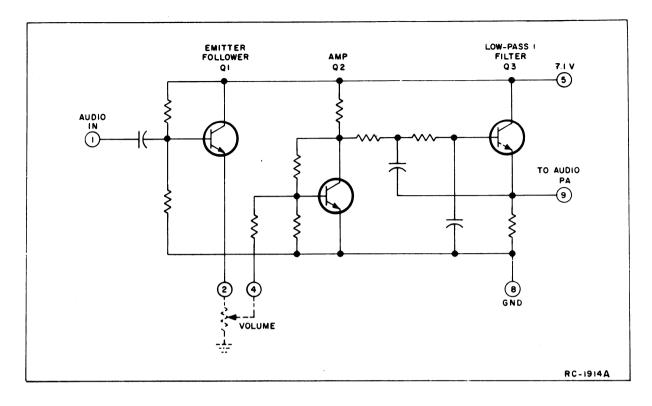


Figure 6 - Typical Audio Amplifier Circuit

AUDIO AMPLIFIER A310

Audio and noise from the discriminator is applied to Audio Amplifier module A310. A typical audio amplifier circuit is shown in Figure 6.

Audio and noise is applied to the base of Ql. This stage operates as an emitter-follower for matching the impedance of the discriminator to the amplifier stage (Q2) and the VOLUME control. The output of Ql connects from Pin 2 to the base of amplifier Q2 (Pin 4) through the VOLUME control. The output of Ql is also applied to the input of the Squelch module.

Following amplifier Q2 is an active low-pass filter (Q3). Audio from the filter is connected from Pin 9 to the Audio PA module. In Audio Amplifier module A310, an active high-pass filter is added in series with the low-pass filter to provide the required tone frequency roll-off.

AUDIO PA A311

When the receiver is quieted by a signal, audio from the active filter is connected to Pin 1 of Audio PA module A311, and then to the base of amplifier Q1. Q1 feeds the audio signal to the base of Q2, which

drives PA transistors Q4 and Q5. A typical audio PA circuit is shown in Figure 7.

PA transistors Q4 and Q5 operate as complementary emitter-followers, providing a 500 milliwatt output into a 8 ohm load. Audio from Pin 9 is coupled through capacitor C302 on the receiver board to the loudspeaker.

SQUELCH A312

Noise from Audio Amplifier A310 operates the squelch circuit. A typical squelch circuit is shown in Figure 8.

When no carrier is present in the receiver, the noise output of active high-pass filter Q1 is coupled to the base of noise amplifier Q2 through SQUELCH control R708. R708 controls the gain of the noise amplifier.

The output of noise amplifier Q2 is detected by diodes CR1 and CR2, and the resultant positive voltage turns off the PNP squelch switch Q3. In standard radios, the emitter of Q3 is connected to +7 Volts by means of a jumper from H1 to H2. When noise turns off Q3, its collector drops to ground potential. As the collector of Q3 is connected to the base of amplifier Q1 in the Audio PA module, turning off Q3 also turns off Q1, keeping the audio PA turned off.

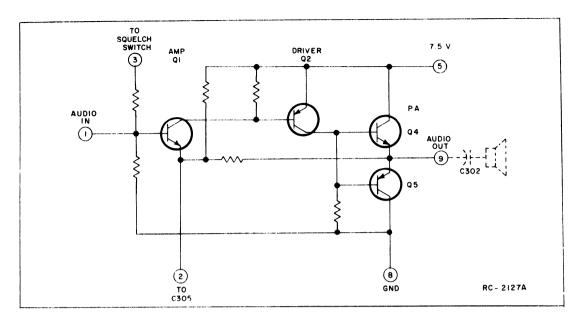


Figure 7 - Typical Audio PA Circuit

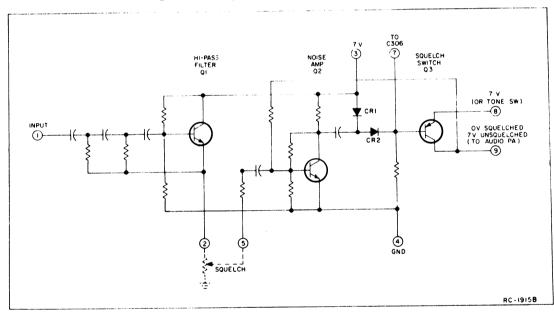


Figure 8 - Typical Squelch Circuit

When the receiver is quieted by a signal, squelch switch Q3 turns on. This applied +7 Volts to the base of amplifier Q1 in the Audio PA module, turning the Audio PA circuit on so that sound is heard at the speaker.

In tone decoder applications, the 7 volt jumper from H1 to H2 is removed. The emitter of squelch switch Q3 is connected

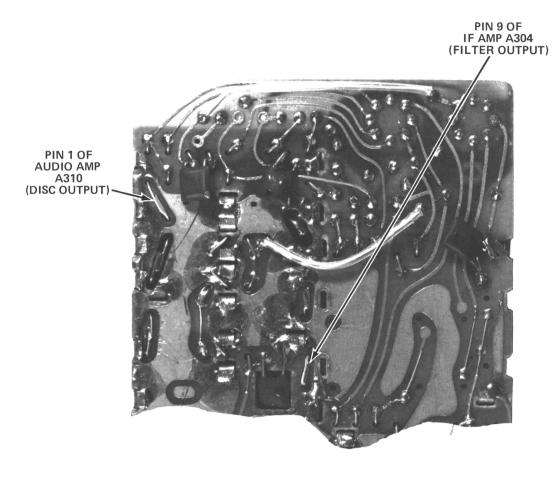
to 7.5 Volts by a DC switch on the decoder board.

An RF adaptor cable is available for connecting the receiver to a signal generator. Connecting the RF adaptor cable to J702 opens a set of contacts on the antenna strip line assembly. This disconnects the antenna and connects the receiver input to J702-1. Connection to chassis ground is made at J702-4.

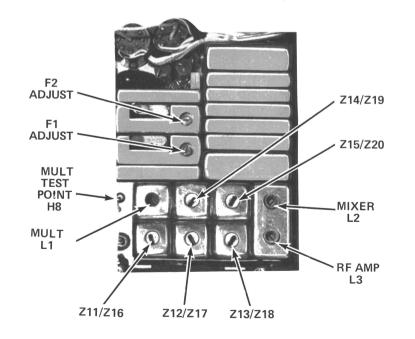
GENERAL ELECTRIC COMPANY+ MOBILE COMMUNICATIONS DIVISION WORLD HEADQUARTERS+LYNCHBURG, VIRGINIA 24502 U.S.A.



LBI4638



COMPONENT SIDE



EQUIPMENT

- A 20 MHz signal source (GE IF Generator Model 4EX9AlO or equivalent) and a 406-470 MHz source connected to Antenna Switch J702 by Receiver Test Cable 19C317633G1.
- 2. GE Test Set Model 4EX3A10 or 4EX8K11 or voltmeter with equivalent sensitivity.
- 3. GE Test Amplifier Model 4EX16A10 and RF probe 19C311370G1, or equivalent RF voltmeter.
- 4. Distortion Analyzer or AC-VTVM.

PRELIMINARY CHECKS AND ADJUSTMENTS

- 1. In multi-frequency receivers where the maximum frequency spacing is less than one MHz, align the receiver of the Fl channel. Where the frequency spacing is more than one MHz, align the receiver on the center frequency.
- 2. Set the slugs in Z11/Z16/Z31 thru Z15/Z20/Z35 to the bottom of the coil form for frequencies in the low end of the band. Set the slugs near the top of the coil form for frequencies near the high end of the band.
- 3. Set the slug in RF AMP L3 to the top of the coil form for frequencies in the low end of the band, and near the bottom of the coil form for frequencies near the high end of the band.
- 4. Connect the negative lead of the DC Test Set to the Mult Test Point (H8), and the positive lead to ground. Connect the Distortion Analyzer or AC-VTVM across the speaker leads.

ALIGNMENT PROCEDURE

C. N	m · 0 · 1	n 1
Step No.	Tuning Control	Procedure
1.	MULT L1	Adjust L1 for maximum meter reading.
2.	Z14/Z19/Z34 and Z15/Z20/Z35	Adjust $214/219/234$ ane then $215/220/235$ for slight change in meter reading.
3.	Z11/Z16/Z31 thru Z13/Z18/Z33 and RF Amp L3	Apply an on-frequency signal to J702 and adjust Z11/Z16/Z23, Z12/Z17/Z32, Z13/Z18/Z33, and L3 for best quieting sensitivity.
4.	Mixer L2	Apply an on-frequency signal as above. With the RF probe on Pin 9 of IF Amp A304, tune L2 for maximum meter reading.
5.	MULT L1 Z14/Z19/Z34 and Z15/Z20/Z35	De-tune Ll. Next, increase the on-frequency input signal and tune 214/219/234 and 215/220/235 for best quieting sensitivity. No re-adjust Ll for maximum meter reading.
		FREQUENCY ADJUSTMENT
6.		While applying an on-frequency signal to J702, loosely couple a 20 MHz signal to the Mixer. Adjust the Oscillator trimmer(s) for a zero beat frequency between the two signals. Alternate Method: Apply a strong 20 MHz signal to the Mixer. Measure the output of the Discriminator with a DC-VTVM at Pin 1 of A310. Note the reading. Next, remove the 20 MHz signal and apply a strong on-frequency signal to J702. Then tune the oscillator trimmer(s) for the meter reading obtained at Pin 1 of A310.

ALIGNMENT PROCEDURE

406—470 MHz RECEIVER TYPES ER60A & ER131B

TEST PROCEDURES

ing --- but not properly. The problems encountered could be low power, poor sensitivity, distortion, and low gain. By following the sequence of test steps starting with Step 1, the defect can be quickly localized.

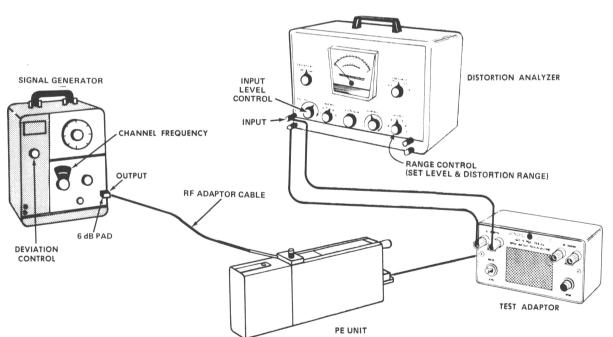
These Test Procedures are designed to help you to service a receiver that is operations of the defective stage is pin-pointed, refer to the "Service Check" listed to correct the problem. Additional corrective measures are included in the Troubleshooting Procedure. Before starting with the Receiver Test Procedures, be sure the receiver is tuned and aligned to the proper operating frequency.

TEST EQUIPMENT REQUIRED

- Distortion Analyzer similar to: Heath IM-12
- Signal Generator similar to: Measurements M-803
- 6-dB attenuation pad
- Test Adaptor Model 4EX12Al0
- RF Adaptor Cable 19C317633G1

PRELIMINARY ADJUSTMENTS

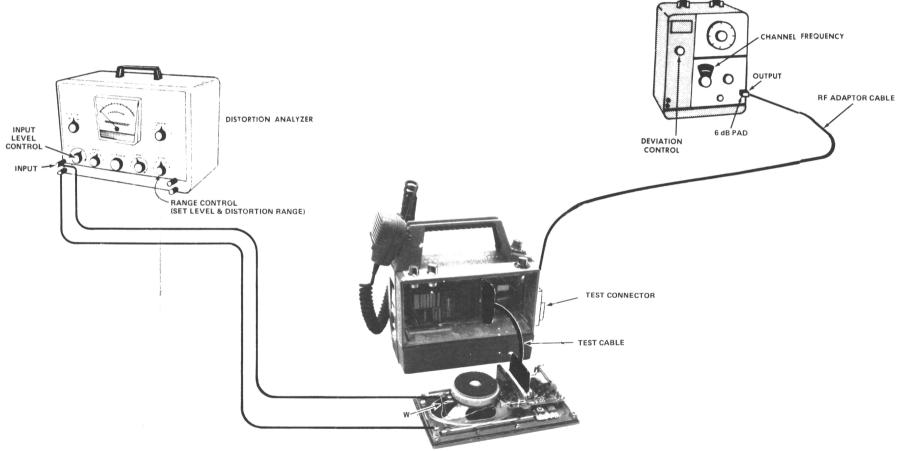
- 1. Connect the test equipment to the receiver as shown for all steps of the receiver Test Procedure.
- 2. Turn the SQUELCH control fully clockwise for all steps of the Test Procedure.
- 3. Turn on all of the equipment and let it warm up for 20 minutes.



NOTE:

To keep from listening to 10 watts of audio, an 8 ohm resistor, rated at more than 10 watts, may be connected between the the white and blue leads on the speaker. When the resistor is used, the white lead is disconnected from the speaker terminal.

SIGNAL GENERATOR



Porta-Mobile II™

STEP 1

AUDIO POWER OUTPUT AND DISTORTION TEST PROCEDURE

Measure Audio Power output as follows:

- A. Connect a 1,000-microvolt test signal modulated by 1,000 hertz ±3.3 kHz deviation to Antenna Switch J702 for PE or J704 for Porta•Mobile II.
- B. Set the PE Volume Control for a 500 milliwatt output (2 volts RMS). Set the Porta•Mobile II Volume Control for 10 Watts output (8.9 Volts RMS).
- C. Make distortion measurements according to test equipment manufacturer's instructions. Reading should be less than 5%-10% for PE (5% is typical). Reading should be less then 10% for Porta•Mobile II. If the receiver sensitivity is to be measured, leave all controls and equipment as they are.

SERVICE CHECK

If the distortion is more than 5% for PE and 10% for Porta Mobile II, or maximum audio output is less than 0.5 watt for PE and 10 watts for Porta Mobile II, make the following checks:

- D. Battery voltage---low voltage will cause distortion. (Refer to Receiver Schematic Diagram for voltages.)
- E. Audio Gain (Refer to Receiver Trouble-shooting Procedure).

STEP 2

USABLE SENSITIVITY (12 dB SINAD) TEST PROCEDURE

If STEP 1 checks out properly, measure the receiver sensitivity as follows:

- A. Apply a 1000-microvolt, on-frequency signal modulated by 1000 Hz with 3.0 kHz deviation to J702.
- B. Place the RANGE switch on the Distortion Analyzer in the 200 to 2000-Hz distortion range position (1000-Hz filter in the circuit). Tune the filter for minimum reading or null on the lowest possible scale (100%, 30%, etc.)
- C. Place the RANGE switch to the SET LEVEL position (filter out of the circuit) and adjust the input LEVEL control for a +2 dB reading on a mid range (30%).
- D. While reducing the signal generator output, switch the RANGE control from SET LEVEL to the distortion range until a 12-dB difference (+2 dB to -10 dB) is obtained between the SET LEVEL and distortion range positions (filter out and filter in).

- E. The 12-dB difference (Signal plus Noise and Distortion to noise plus distortion ratio) is the "usable" sensitivity level. The sensitivity should be less than rated 12 dB SINAD specification with an audio output of at least 250 milliwatts.
- F. Leave all controls as they are and all equipment connected if the Modulation Acceptance Bandwidth test is to be performed.

SERVICE CHECK

If the sensitivity level is more than rated 12 dB SINAD, check the alignment of the RF stages as directed in the Alignment Procedure, and make the gain measurements as shown on the Troubleshooting Procedure.

STEP 3

MODULATION ACCEPTANCE BANDWIDTH (IF BANDWIDTH)

TEST PROCEDURE

If STEPS 1 and 2 check out properly measure the bandwidth as follows:

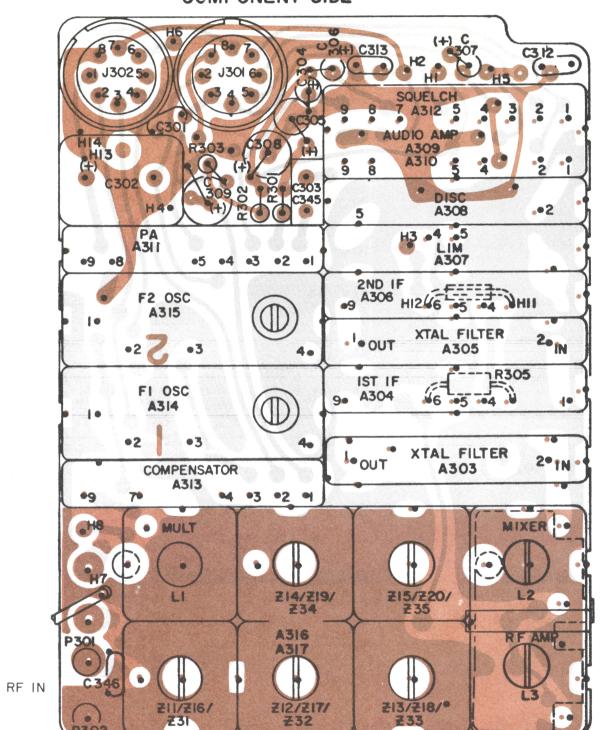
- A. Set the Signal Generator output for twice the microvolt reading obtained in the 12-dB SINAD measurement.
- B. Set the RANGE control on the Distortion Analyzer in the SET LEVEL position (1000-Hz filter out of the circuit), and adjust the input LEVEL control for a +2 dB reading on the 30% range.
- C. While increasing the deviation of the Signal Generator, switch the RANGE control from SET LEVEL to distortion range until a 12-dB difference is obtained between the SET LEVEL and distortion range readings (from +2 dB to -10 dB).
- D. The deviation control reading for the 12-dB difference is the Modulation Acceptance Bandwidth of the receiver. It should be more than ±7 kHz (but less than ±9 kHz).

SERVICE CHECK

If the Modulation Acceptance Bandwidth test does not indicate the proper width, make gain measurements as shown on the Receiver Troubleshooting Procedure.

	PIN	PIN 2	PIN 3	PIN 4	PIN 5	PIN 6	PIN 7	PIN 8
J301	5.4V	AUDIO OUT	SWITCHED 7.5V	SQ ARM	VOL ARM	SQ HI	VOL H I	GND
J302		FREQ I	FREQ 2			7.5V	TONE SWITCH	GND

COMPONENT SIDE



RUNS ON BOTH SIDES - RUNS ON COMPONENT SIDE

- RUNS ON SOLDER SIDE

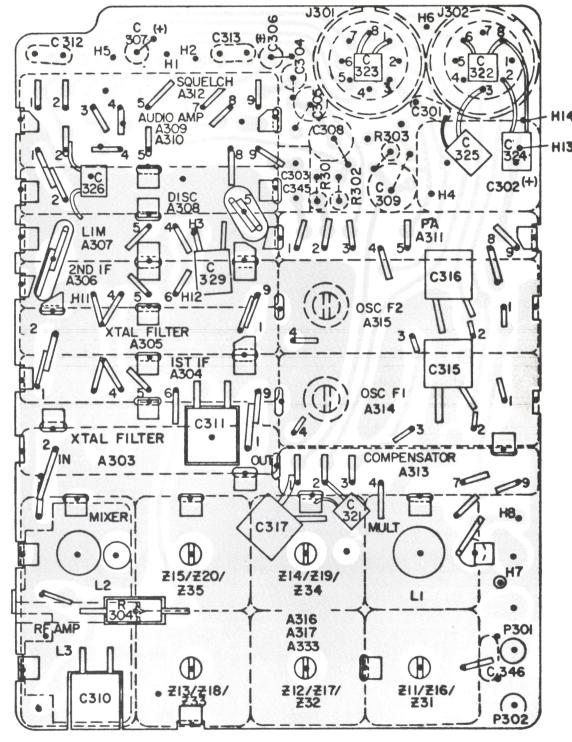
OUTLINE DIAGRAM

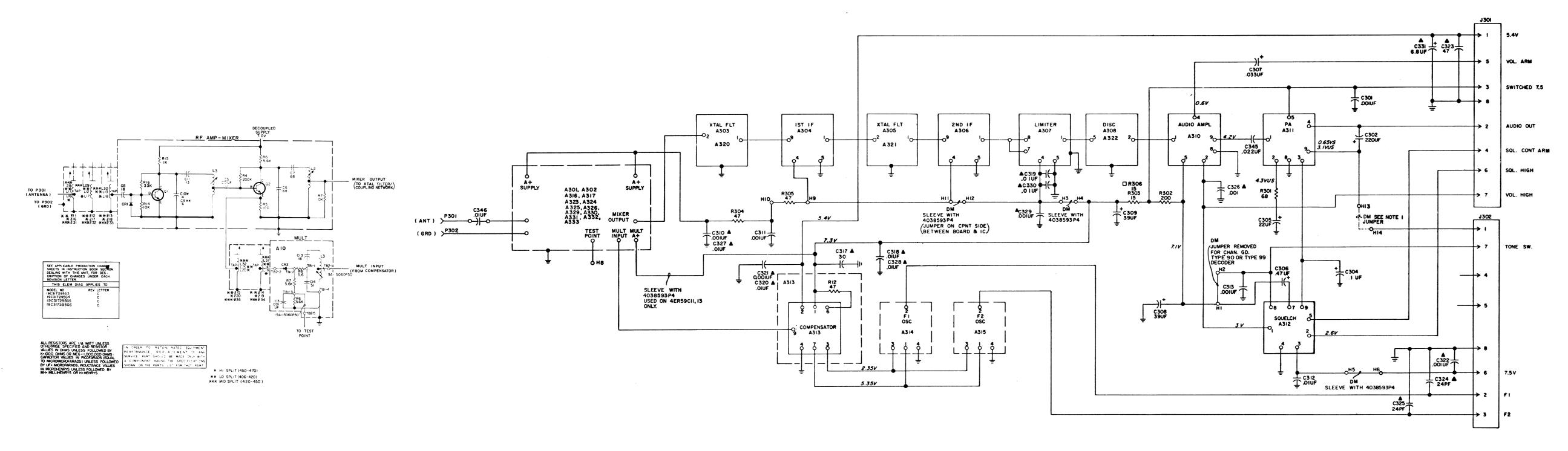
406—470 MHz RECEIVER TYPES ER60A & ER131B

(19D416913, Rev. 13) (19D416852, Sh. 2, Rev. 5) (19D416852, Sh. 3, Rev. 6)









(19C320887, Rev. 8)

SCHEMATIC DIAGRAM

SEE APPLICABLE PRODUCTION CHANGE SHEETS IN INSTRUCTION BOOK SECTION DEALING WITH THIS UNIT, FOR DES-CRIPTION OF CHANGES UNDER EACH REVISION LETTER. REVISION LETTER.

THIS ELEM DIAG APPLIES TO

MODEL NO ______ BEY LETTER ___
PLI9D417490GI MODEL NO _____PLI9D417490GI PL19D417490G2 PLI9 D417490G3 PLI9AI30042G1 PLI9AI30042G2 PLI9AI30042G3 PLI9AI30042G4 PLI9AI30042G5 PLI9AI30042G6

NOTE 1: DM JUMPER ON SOLDER SIDE H13 TO H14. PRESENT IN PM II APPLICATIONS ONLY.

▲ PART OF MODIFICATION KIT PLI9AI30042 SEE CHART BELOW FOR SELECTION OF PRUPER PARTS FOR APPLICABLE MODEL NO.

MODEL NO.	C310	C315	C316	C317	C318	2319	C320	C321	C322	C323	C324	C325	C326	C327	C328	C329	C330	C331	2
4ER59A10-13 (KIT PL19A130042G1)	×												x						Γ
4ER60AIO-13 (KIT PLI9AI30042G2)	×			×				,	x	х	×	x	х			x			Γ
4ER6!AII- 13 - 15 - 17 (KIT PLI9A30042G3)						×	×						×	×	x				
4ER62A10-11 (KIT PL19A130042G4)	×			x	x		x					-	x						Г
4ER59CII,13 (KIT PL19A130042G5)	x					x		x					x		х		х	x	Г
4ER87A10-13 (KIT PL19A130042G6)						x	x						х	x	x				

IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART.

VOLTAGE READINGS ALL READINGS TAKE WITH A DC-VTVM
AND MEASURED TO GROUND. READINGS
FOLLOWED BY "S" ARE WITH THE RECEIVER
SQUELCHED. READINGS FOLLOWED BY "US"
ARE WITH THE RECEIVER UNSQUELCHED.

SCHEMATIC DIAGRAM

406-470 MHz RECEIVER TYPES ER60A & ER131B

Issue 10

406-470 MHz RECEIVER FRONT END (A316/A317/A333) TYPES ER60A & ER131B

PARTS LIST

LB14381K

YMBOL	GE PART NO.	DESCRIPTION
316* nd 317*		FRONT END 19C317295G5 406-420 MHz 19C317295G6 450-470 MHz (Added by REV A) 19C317295G12 420-450 MHz
A5* and A6*		RF AMPLIFIER A5 19C327300G3 406-450 MHz A6 19C327300G4 450-470 MHz (Added by REV C)
05	5405202010	
C5 C6	5495323P12 19A700223P59	Ceramic: 0.001 uF +100% -20%, 75 VDCW. Ceramic: 6.8 pF +5%, 100 VDCW, temp coef
and C7	194700223539	-220 PPM.
C8	19A700225P38	Ceramic: 18 pF ±5%, 100 VDCW, temp coef -470 PPM.
C9	19A116114P2020	Ceramic: 6 pF ±5%, 100 VDCW, temp coef -80 PPM.
C10	19A116114P2014	Ceramic: 4 pF ±5%, 100 VDCW; temp coef -80 PPM.
C11	19A700221P32	Ceramic: 13 pF ±5%, 100 VDCW, temp coef -80 PPM.
		DIODES AND RECTIFIERS
CR1*	19A116052P1	Silicon, hot carrier: Fwd drop .350 volts max. Added by REV B.
L2	19B216948G1	Coil.
L3	19A128005G1	Coil. Includes:
	19B209436P1	Tuning slug.
Q1 and Q2	19A116159P1	Silicon, NPN.
		RESISTORS
R4	3R151P204J	Composition: 200K ohms ±5%, 1/8 w.
R5	3R151P101J	Composition: 100 ohms $\pm 5\%$, 1/8 w.
R6	3R151P562J	Composition: 5.6K ohms ±5%, 1/8 w.
R7	3R151P103J	Composition: 10K ohms ±5%, 1/8 w.
R14	3R151P103J	Composition: 10K ohms ±5%, 1/8 w.
R15	3R151P102J	Composition: 1K ohms ±5%, 1/8 w. Composition: 33K ohms +5%, 1/8 w.
R16	3R151P333J	Composition: 33K ohms ±5%, 1/8 w.
A5* and A6*		RF AMPLIFIER A5 19C317445G3 406-450 MHz A6 19C317445G4 450-470 MHz (Deleted by REV C)
C5	5495323P12	Ceramic: 0.001 uF +100% -20%, 75 VDCW.
C6 and C7	19A116114P4059	Ceramic: 68 pF ±5%, 100 VDCW, temp coef -220 PPM.
C8	19A116114P6038	Ceramic: 18 pF ±5%, 100 VDCW, temp coef -470 PPM.
С9	19A116114P2020	Ceramic: 6 pF ±5%, 100 VDCW, temp coef -80 PPM.
C10	19A116114P2014	Ceramic: 4 pF +5%, 100 VDCW; temp coef -80 PPM.
C11	19A116114P2035	Ceramic: 13 pF ±5%, 100 VDCW; temp coef -80 PPM.

YMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
CR1*	19A116052P1	DIODES AND RECTIFIERS	L17 L18	19B216439G2 19C311750P1 19B216439G1 19C311750P1	Helical resonator. (Part of Z17). Includes Tuning slug. Helical resonator. (Part of Z18). Includes Tuning slug.
L2 L3	19B216948G1 19A128005G1	Coil. Includes:	L19	19B216439G4 19C311750P1	Helical resonator. (Part of 219). Included Tuning slug.
	19B209436P1	Tuning slug. TRANSISTORS Silicon, NPN.	L20 L28 L29	19B216439G3 19C311750P1 19B233677G2 19B233677G3	Helical resonator. (Part of Z20). Include: Tuning slug. Helical resonator. (Part of Z28). Helical resonator. (Part of Z29).
Q1 and Q2 R4	19 A 116159P1		L30 L31 L32	19B233677G1 19B216439G15 19B216439G14	Helical resonator. (Part of 7.23). Helical resonator. (Part of 7.31). Helical resonator. (Part of 7.32).
R5 R6	3R151P101J 3R151P562J	Composition: 100 ohms ±5%, 1/8 w. Composition: 5.6K ohms ±5%, 1/8 w.	211	10,0210433014	HELICAL RESONATORS Consists of L11 and 19D413132P24 can.
R7 R14 R15	3R151P103J 3R151P103J 3R151P102J	Composition: 10K ohms ±5%, 1/8 w. Composition: 10K ohms ±5%, 1/8 w. Composition: 1K ohms ±5%, 1/8 w.	Z12 Z13 Z14		Consists of L12 and 19D413132P3 can. Consists of L13 and 19D413132P25 can. Consists of L14 and 19D413132P19 can.
R16	3R151P333J	Composition: 33K ohms <u>+</u> 5%, 1/8 w. MULTIPLIER 19C311873G7	Z15 Z16 Z17		Consists of L15 and 19D413132P20 can. Consists of L16 and 19D413132P24 can. Consists of L17 and 19D413132P3 can.
C3 C13	5495323P12 19A700221P38		Z18 Z19 Z20		Consists of L18 and 19D413132P25 can. Consists of L19 and 19D413132P19 can. Consists of L20 and 19D413132P20 can.
C14	19A700221P54	Ceramic: 51 pF ±5%, 100 VDCW, temp coef -80 PPM. DIODES AND RECTIFIERS Silicon; sim to HP Step Recovery 5082-0180.	Z31 Z32 Z33		Consists of L28 and 19D413132P24 can. Consists of L29 and 19D413132P3 can. Consists of L30 and 19D413132P25 can.

SYMBOL | GE PART NO.

CR1 19A116081P1

Z17

Z18

----- RESISTORS ------

Composition: 180K ohms ±5%, 1/8 w.

Composition: 3K ohms $\pm 5\%$, 1/8 w.

	R5	3R151P101J	Composition: 100 onms ±5%, 1/8 w.	1	1			1	- 1
	R6	3R151P562J	Composition: 5.6K ohms ±5%, 1/8 w.		Z11		Consists of L11 and 19D413132P24 can.		
-	R7	3R151P103J	Composition: 10K ohms ±5%, 1/8 w.		Z12		Consists of L12 and 19D413132P3 can.	1	L1
	R14	3R151P103J	Composition: 10K ohms ±5%, 1/8 w.		Z13		Consists of L13 and 19D413132P25 can.		
	R15	3R151P102J	Composition: 1K ohms ±5%, 1/8 w.		Z14		Consists of L14 and 19D413132P19 can	١.	_
	R16	3R151P333J	Composition: 33K ohms ±5%, 1/8 w.		Z15		Consists of L15 and 19D413132P20 can.	1 8	R1 and
PM.			MULTIPLIER		Z16		Consists of L16 and 19D413132P24 can.	Ι '	R2
	A10		19C311873G7		Z17		Consists of L17 and 19D413132P3 can.		
					Z17 Z18		Consists of L18 and 19D413132P25 can.		
м.		5.405000D10	Ceramic: 0.001 uF +100% -20%, 75 VDCW.		- 1		Consists of L19 and 19D413132P19 can.	1	
-	C3	5495323P12	Ceramic: 18 pF ±5%, 100 VDCW, temp coef -80 PPM.		719		Consists of L20 and 19D413132P20 can.		i
	C13	19A700221P38	Ceramic: 51 pF ±5%, 100 VDCW, temp coef -80 PPM.		Z20		Consists of L28 and 19D413132P24 can.	L1	1
	C14	19A700221P54	ceramic: 51 pr +5%, 100 vbc#, temp coel -80 rr#.		Z31 Z32		Consists of L29 and 19D413132P24 can.		
-			DIODES AND RECTIFIERS		Z32 Z33		Consists of L30 and 19D413132P25 can.	L1:	2
	CR2	19A116809P1	Silicon; sim to HP Step Recovery 5082-0180.		Z33 Z34		Consists of L31 and 19D413132P19 can.		
					Z34 Z35		Consists of L32 and 19D413132P19 can.	L1:	3
		10001000000			235		Consists of E.52 and 190413132P20 can.		
- 1	L3	19B216296P3	Coil.		A316*		FRONT END 19C317293G3 406-420 MHz	L1	4
-			RESISTORS		and A317*		19C317293G3 400-420 MHz 19C317294G4 450-470 MHz (Deleted by REV A)	1	
- 1	R6*	3R151P562J	Composition: 5.6K ohms ±5%, 1/8 w. Deleted by				(beteved by REV N)	L1	5
- 1		0015105001	REV A. Composition: 5.6K ohms ±5%, 1/8 w.	Ш	A5		RF AMPLIFIER A5 19C317445G3		
-	R7	3R151P562J	Composition: 5.6 ohms ±5%, 1/8 w.		and A6		A6 19C317445G4	L10	6
	R8	3R151P5R6J	Composition: 5.6K ohms +5%, 1/8 w. Added by	П					
- 1	R10*	3R151P562J	REV A.		C5	5495323P12	Ceramic: 0.001 uF +100% -20%, 75 VDCW.	L1	⁷
			MISCELLANEOUS		C6	19A116114P4059	Ceramic: 68 pF ±5%, 100 VDCW, temp coef -220 PPM.		
		19B200497P5	Tuning slug. (Used with L3).		and C7	19411611474039	Ceramic. do pr -da, 100 vbcm, temp coer 220 rrain	L1	8
- 1		19820049773	Tuning Sing. (Used with 13).	11	C8	19A116114P6038	Ceramic: 18 pF +5%, 100 VDCW; temp coef -470 PPM.	l	
				Н	C9	19A116114P2020	Ceramic: 6 pF +5%, 100 VDCW, temp coef -80 PPM.	L1	9
- 1	L11	19B216439G8	Helical resonator. (Part of Z11). Includes:		C10	19A116114P2014	Ceramic: 4 pF +5%, 100 VDCW; temp coef -80 PPM.		
		19C311750P1	Tuning slug.		C10	19A116114P2035	Ceramic: 13 pF +5%, 100 VDCW; temp coef -80 PPM.	L2	°
İ	L12	19B216439G6	Helical resonator. (Part of Z12). Includes:	11		13411011472033	ceramic. In pr _ov, 100 voes, cemp over 50 tras	1	
		19C311750P1	Tuning slug.					1	
	L13	19B216439G19	Helical resonator. (Part of Z13). Includes:	П	L2	19B216948G1	Coil.	Z1	1
-		19C311750P1	Tuning slug.		L3	19A128005G1	Coil. Includes:	Z1	2
	L14	19B216439G22	Helical resonator. (Part of Z14). Includes:			19B209436P1	Tuning slug.	21	3
PPM.		19C311750P1	Tuning slug.					Z1	4
	L15	19B216439G21	Helical resonator. (Part of Z15). Includes:		.,	19A116159P1	Silicon, NPN.	Z1	.5
PM.		19C311750P1	Tuning slug.	$ \ $	Q1 and	19811013981	Stiteon, Mrn.	Z1	.6

R1 3R151P184J

R2 3R151P302J

L16 19B216439G7 Helical resonator. (Part of Z16). Includes:

Tuning slug.

19C311750P1

GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBO
3R151P204J	Composition: 200K ohms ±5%, 1/8 w.	Z19		Consists of L19 and 19D413132P19 can.	C312*
3R151P101J	Composition: 100 ohms ±5%, 1/8 w.	Z20		Consists of L20 and 19D413132P20 can.	1
3R151P562J	Composition: 5.6K ohms ±5%, 1/8 w.				
3R151P103J	Composition: 10K ohms ±5%, 1/8 w.			RECEIVER BOARD	
				19D417490G1 REV M 19D417490G3 REV K	C313
	MULTIPLIER 19C311873G6			1	C314*
		A303*	19C304824G1	Crystal filter.	C345*
				In REV C and earlier:	
5495323P12	Ceramic: 0.001 uF +100% -20%, 75 VDCW.		19C304516G3	Crystal filter.	C346*
19A116114P2050	Ceramic: 39 pF ±5%, 100 VDCW, temp coef -80 PPM.	A304	19C311879G3	1st IF Amplifier.	
19A116114P7065	Ceramic: 100 pF ±5%, 100 VDCW, temp coef -750 PPM.	1			
	DIODES AND RECTIFIERS	A305*	19C304824G1	Crystal filter.	J301 and
10111000101			10020450802	In REV A and earlier:	J302
19A116081P1	Silicon.	1	19C304508G3	Crystal Filter.	
	INDUCTORS	A306	19C311879G4	2nd IF Amplifier.	P301 and
19B216296P1	Coil.			1/2/2-2	P302
	PAGA SERONG	A307	19C311876G4	Limiter.	
		A308	19C304504G3	Discriminator.	R301*
3R151P432J	Composition: 4.3K ohms ±5%, 1/8 w.	A309*	19C311878G2	Audio Amplifier. Deleted by REV H.	
	MISCELLANEOUS	A310*	19C330341G1	Audio Amplifier.	1
19B200497P5	Tuning slug.	ASTO.	13033034101	In REV H:	}
19820043773	Tuning Stuge	1	19C311995G4	Audio Amplifier.	R302
			19031139304	In REV G & earlier:	R303*
19B216439G8	Helical resonator. (Part of Z11). Includes:	1	19C311995G2	Audio Amplifier. (Includes Tone Filter).	R304
19C311750P1	Tuning slug.	1	13031133002	made imprise (include fone transfer	R305
19B216439G6	Helical resonator. (Part of Z12). Includes:	A311*	19C330710G1	PA.	R306*
19C311750P1	Tuning slug.		l	In REV F & earlier:	R306*
19B216439G19	Helical resonator. (Part of Z13). Includes:	1	19C311877G2	PA.	1
19C311750P1	Tuning slug.	A312*	19C330342G1	Squelch.	1
19B216439G4	Helical resonator. (Part of Z14). Includes:	A312	13033034231	In REV H & earlier:	
19C311750P1	Tuning slug.	1	19C311880G4	Squelch.	1
19B216439G3	Helical resonator. (Part of Z15). Includes:	1	19031100004	bquetent	
19C311750P1	Tuning slug.	A313*	19C320061G1	Compensator.	
19B216439G7	Helical resonator. (Part of Z16). Includes:	İ		In REV B & earlier:	
19C311750P1	Tuning slug.	l	19C311891G5	Oscillator Compensator.	C310
19B216439G2	Helical resonator. (Part of Z17). Includes:	A320	19C304824G3	Band Pass Filter.	C315*
19C311750P1	Tuning slug.	and A321	13030402100	24.4 14.5 111611	C316*
19B216439G1	Helical resonator. (Part of Z18). Includes:	A322	19C304504G6	Discriminator.	C317
19C311750P1	Tuning slug.	1.022			C321 and
19B216439G4	Helical resonator. (Part of Z19). Includes:			CAPACITORS	C322
19C311750P1	Tuning slug.	C301	5495323P12	Ceramic: 0.001 uF +100% -20%, 75 VDCW.	C323
19B216439G3	Helical resonator. (Part of Z20). Includes:	C302	19A116178P7	Tantalum: 220 uF ±20%, 6 VDCW.	C324
19C311750P1	Tuning slug.	C303*	19A116089P1	Ceramic: 0.1 uF ±20%, 50 VDCW, temp range -55 to +85°C. Deleted by REV H.	and C325
	HELICAL RESONATORS	C304	5491674P28	Tantalum: 1 uF \pm 20%, 25 VDCW; sim to Sprague Type 162D.	C326
	Consists of L11 and 19D413132P24 can. Consists of L12 and 19D413132P3 can.	C305	5491674P35	Tantalum: 22 uF ±20%, 4 VDCW; sim to Sprague Type 162D.	C329
	Consists of L13 and 19D413132P25 can.	C306	5491674P27	Tantalum: 0.47 uF ±20%, 35 VDCW; sim to Sprague	
	Consists of L14 and 19D413132P19 can.			Type 162D.	
	Consists of L15 and 19D413132P20 can.	C307	5491674P31	Tantalum: 0.033 uF ±20%, 35 VDCW; sim to Sprague Type 162D.	
	Consists of L16 and 19D413132P24 can.	C308	5491674P30	Tantalum: 39 uF ±20%, 10 VDCW; sim to Sprague	
	Consists of L17 and 19D413132P3 can.	and C309		Type 162D.	
	Consists of L18 and 19D413132P25 can.	C311	5495323P12	Ceramic: 0.001 uF +100% -20%, 75 VDCW.	
		1	1	1	1

1BOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
*	19A116192P1	Ceramic: 0.01 uF ±20%, 50 VDCW; sim to Erie 8121 Special.			ASSOCIATED ASSEMBLIES
· ·	5495323P12 5495323P12 5495323P12 19A116192P6 19A116192P1	In REV A & earlier: Ceramic: 0.001 uF +100% -20%, 75 VDCW. Ceramic: 0.001 uF +100% -20%, 75 VDCW. Ceramic: 0.001 uF +100% -20%, 75 VDCW. Deleted by REV E. Ceramic: 0.022 uF +20%, 50 VDCW; sim to Erie 8131-M050-W5R-223M. Added by REV H. Ceramic: 0.01 uF +20%, 50 VDCW; sim to Erie 8121	A314 and A315	4EG28A12	OSCILLATOR MODULES USED IN PE APPLICATIONS NOTE: When reordering, give GE Part Number and specify exact frequency needed. Oscillator Module. 406-450 MHz. Fx = Fo + 20
	190331182P1	Special. Added by REV K. JACKS AND RECEPTACLES Connector: 8 pins.		4EG28A13	Oscillator Module. 450-470 MHz. $Fx = \frac{Fo - 20}{21}$ OSCILLATOR MODULES USED IN PORTA MOBILE II
2	194115834P4		A314, A315, and A1		APLICATIONS NOTE: When reordering, give GE Part Number and specify exact frequency ne ded.
2			thru A10	4EG38A10	Oscillator Module. 406-450 MHz. Fx = $\frac{\text{Fo} + 20}{21}$
*	3R151P680J	Composition: 68 ohms ±5%, 1/8 w. In REV A-D:		4EG38A11	Oscillator Module. 450-470 MHz. $Fx = \frac{Fo - 20}{21}$
	3R151P101J	Composition: 100 ohms ±5%, 1/8 w. Earlier than REV A:			
	3R151P470J	Composition: 47 ohms ±5%, 1/8 w.			
2 3*	3R151P201J 3R151P150J	Composition: 200 ohms ±5%, 1/8 w. Composition: 15 ohms ±5%, 1/8 w. Deleted by REV L.			
	19A134231P470J	Deposited carbon: 47 ohms ±5%, 1/8 w.	1		
5	3R151P470J	Composition: 47 ohms ±5%, 1/8 w.	1		
3*	19A134564P1	Metal film: 15 ohms ±5%, 1/4 w. Added by REV L.			
	19A129132P1	Shield. (Used with A5-A7).			
	19B216316P1	Insulator. (Used with J301 & J302).			
		CAPACITOR KIT 19A130042G2			
,	5495323P12	Ceramic: 0.001 uF +100% -20%, 75 VDCW.			
5* 5*	5495323P12	Ceramic: 0.001 uF +100% -20%, 75 VDCW. Deleted by REV A.			
7	19A700226P45	Ceramic: 30 pF ±5%, 100 VDCW, temp coef -750 PPM.			
l 2	5495323P12	Ceramic: 0.001 uF +100% -20%, 75 VDCW.			
3	19A700227P53	Ceramic: 47 pF ±5%, 100 VDCW, temp coef -1500 PPM.			
5	19A700221P42	Ceramic: 24 pF ±5%, 100 VDCW, temp coef -80 PPM.			
5	5495323P12	Ceramic: 0.001 uF +100% -20%, 75 VDCW.			

Ceramic: 0.001 uF +100% -20%, 75 VDCW.

5495323P12

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

- REV. A 4ER60A10-13 To improve design. Changed A316 and A317.
- REV. B To improve squelch action. Changed A305.
- REV. C To suppress harmonics from IF limiter. Added C329.
- REV. A Receiver Board 19D417490G1
 To increase audio sensitivity.
 Changed R301.
- REV. A Receiver Front End 19C317295G5 & 6

 To improve receiver spurious response.
 Deleted R2 and R6. Added shield.
- REV. B Receiver Board 19D417490G1

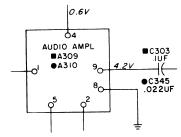
 To improve critical squelch operation.
 Changed C312.
- REV. C To eliminate spurious when keyed. Changed A313.
- REV. B Receiver Front End 19C317295G5 & 6

 To add base protection for transistor Q1.
 Added CR1.
- REV. C To improve ease of assembly, troubleshooting and repair. Changed A5 and A6.
- REV. D Receiver Board 19D417490G1

 To improve factory producibility.
 Changed A303.
- REV. E To improve audio sensitivity and stability.
 Deleted C314 and changed R301.
- REV. F To improve audio frequency response and attack time. Add C345 to be used with Channel Guard.
- REV. G To improve audio quality. Changed A311.
- REV. H To eliminate Non-Channel Guard receiver boards.
 Deleted callout of #A3009 and circle (*) in
 front of A310. Deleted callout of #C303 and
 circle (*) for C345.

 Deleted Notes: #Use for Non-Channel Guard receivers
 and * use for Channel Guard receivers.

Schematic Diagram Was:



- REV. A Receiver Kit 19A130042G2

 To improve reliability. Deleted C315 and C316.
- REV. J Receiver Board 19D417490G1
 -- VOID--
- REV. K To provide DC isolation of relay receive contacts from antenna circuit.
 Added C346.
- REV. L To incorporate flame-proof resistors. Deleted R303. Added R306.
- REV. M To implement improved hybrid packaging technique. Changed A310, A311 and A312.
- REV. A thru K Receiver Board 19D417490G3
 Incorporated into initial shipment.

REV. N - Receiver Board 19D417490G1
REV. L - Receiver Board 19D417490G3
To improve squelch switch.
Changed A312 and C304.

Components Were:

A312: C330342G1, Squelch. C304: Tantalum 1.0 μ f \pm 20%, 25VDCW.

REV. P - Receiver Board 19D417490G1 REV. L - Receiver Board 19D417490G3 To eliminate "bubbling" at critical squelch. Changed A312 and C304.

Components were:

A312: 19C330342G2, Squelch. C304: Tantalum, 3.3 µf ± 20%, 10VDCW.

REV. R - Receiver Board 19D417490G1 REV. N - Receiver Board 19D417490G3

To improve test and troubleshooting. Added H13 and H14, and changed connection of A304-4 from H10 to H9.

211/216/ 231 (RC-2150) (19D416913, Rev. 13) (19D416853, Sh. 2, Rev. 5) VOLTAGE

QUICK CHECKS

SYMPTOM	PROCEDURE
No Audio	1. Check audio waveform at the top of the Volume Control (see Step 2).
	 If audio is present, check voltage readings of Audio and Squelch modules (see Schematic Diagram).
	 If audio is not present, check gain and current readings of Front End and IF modules (see Steps 1 & 3).
Poor Sensitivity	1. Measure the gain of the Mixer stage (see Step 3). If low, measure the gain of th RF amplifier and IF modules.
Improper Squelch Operation	1. Check the noise waveform at the input to the Squelch module and at Squelch Con- trol high (see Step 2).
	Measure the DC voltages for the Squelch module (squelched and unsquelched).

STEP 3-RF GAIN CHECKS (STEPS Q THRU U)

STEP 3 - RF GAIN CHECKS EQUIPMENT REQUIRED:

- RF probe and Test Amplifier Model 4EX16A10 connected to GE Test Set Model 4EX3A10, or an RF voltmeter.
- A signal generator (M-800 or equivalent) connected to P301 (High) and P302 (Low).

PROCEDURE FOR MIXER & 1ST IF:

- 1. Switch the Test Set to the Test 1 position and the Test Amplifier
- 2. Connect the RF probe across the input of the stage to be measured as shown on the diagram. Increase the signal generator output to obtain a reference reading on Test Set 4EX3AlO. Note the Test Set reading and the dB reading on the generator (dB1).
- 3. Connect the RF probe to the output of the stage to be measured as shown on the diagram. Decrease the generator output until the Test Set reference reading in Step 2 is obtained. Note the dB reading on the generator (dB2).
- 4. Subtract the dBl reading from the dB2 reading and check the results with the typical gains shown on the diagram.

Example:
$$\begin{array}{c} 35 \text{ dB } \text{(dB2)} \\ -15 \text{ dB} \text{(dB1)} \\ \hline 20 \text{ dB} \text{ gain} \end{array}$$

PROCEDURE FOR 2ND IF:

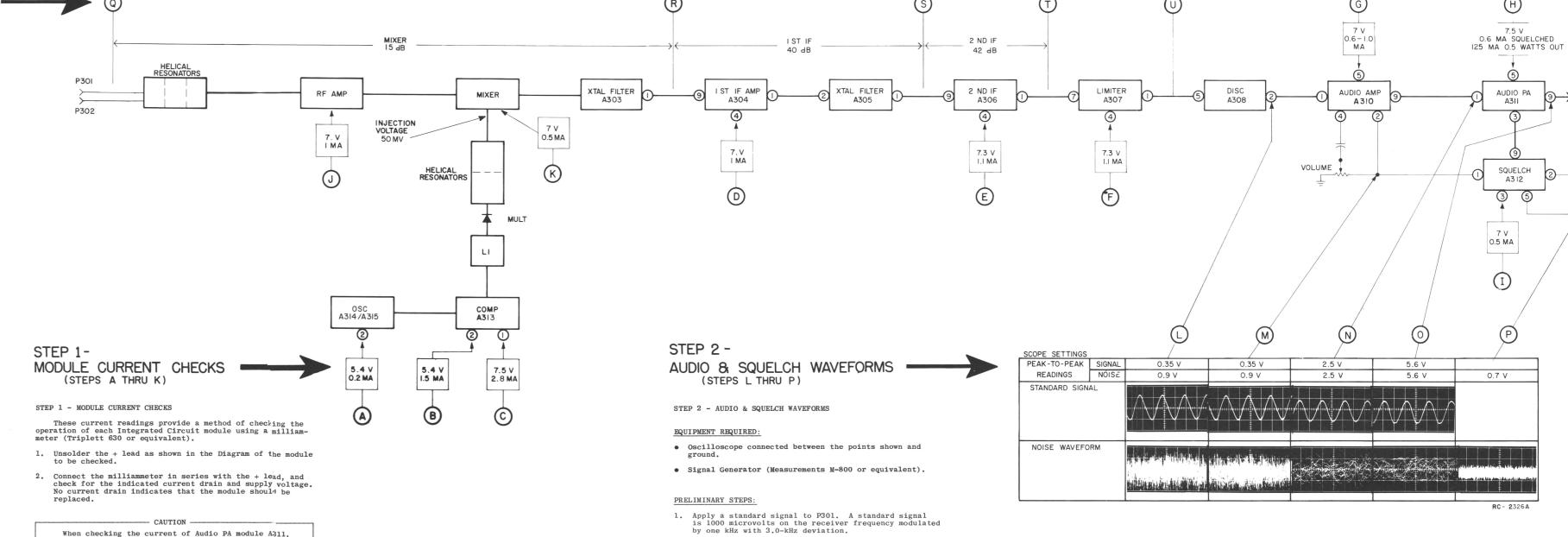
- 1. With no signal in, connect the RF probe to the output of the 2nd IF module. Increase the signal generator output until the Test Set reading increases by approximately 0.2 volt. Note Test Set and signal generator reading (dB2).
- Connect the probe to the input of the 2nd IF module. Increase the signal generator until the Test Set reference reading is obtained, and note the dB reading (dBl).
- 3. Now subtract dB2 from dB1 to obtain the gain of the 2nd IF amplifier module.

The Limiter module limits on noise so that he gain of the circuit cannot be measured. The following procedure provides a check to determine if the module is limiting.

- Switch the Test Amplifier to the Xl position and the Test Set to the Test 1 position. Then connect the RF probe to the output of the Limiter module and check for a reading of approximately 0.4
- 2. Increase the signal generator output. There should be no appreciable increase in the limiter output meter reading.

--- CAUTION --When checking the current of Audio PA module A311, do not short Pin 4 to ground or to + (Pin 5). To

do so will destroy the Audio PA module.



2. Set the Volume control for 0.5-watt output.

1200BLESHOOTING PROCEDURE

406—470 MHz RECEIVER TYPES ER60A & ER131B